Abstracts

Hybrid Mode Analysis of RF Characteristics in Integrated Optical Modulators on III-V Semiconductors

K. Wu, C.-Y.E. Tong and R. Vahldieck. "Hybrid Mode Analysis of RF Characteristics in Integrated Optical Modulators on III-V Semiconductors." 1990 MTT-S International Microwave Symposium Digest 90.1 (1990 Vol. I [MWSYM]): 289-292.

The method of lines has been applied to study the RF/-microwave characteristics of III-V semiconductor traveling wave electrooptic modulators. Double-rib, multilayer strip wave-guides have been investigated. It is found that Schottky barrier junction controlled structures support multi-nondispersive modes having phase velocities that closely match the optical carrier, These modes are potentially useful in ultra-fast modulators operating into the millimeter wave band.

❑ Return to main document.